

## **AMENDMENTS TO THE CLAIMS**

The following listing of claims replaces all prior versions, and listings, of claims in the application:

Claims 1-19 (Cancelled)

20. (New) A nitride based heterostructure device comprising:

a substrate;

a buffer layer on the substrate, wherein the buffer layer includes In; and

a quaternary layer on the buffer layer, wherein the quaternary layer includes Ga, Al, N, and In.

21. (New) The device of claim 20, wherein the substrate comprises one of the group comprising sapphire, SiC, ZnO, a spinel substrate, Si, anodized alumina, and AlN.

22. (New) The device of claim 20, wherein the quaternary layer includes about a 20% to 30% molar fraction of Al.

23. (New) The device of claim 22, wherein the quaternary layer further includes about a 2% to 5% molar fraction of In.

24. (New) A nitride based heterostructure device comprising:
- a substrate;
  - a buffer layer on the substrate, wherein the buffer layer includes In;
  - a first layer including GaN on the buffer layer;
  - a second layer on the first layer, wherein the second layer includes AlGaN; and
  - a quaternary layer on the second layer, wherein the quaternary layer includes AlInGaN.
25. (New) The device of claim 24, wherein the substrate includes one of the group comprising sapphire, SiC, ZnO, a spinel substrate, Si, anodized alumina, and AlN.
26. (New) The device of claim 24, wherein the quaternary layer includes about a 20% to about 30% molar fraction of Al.
27. (New) The device of claim 26, wherein the quaternary layer further includes about a 2% to about 5% molar fraction of In.
28. (New) The device of claim 24, wherein the first layer further includes In.

29. (New) A nitride based heterostructure device comprising:

a substrate;

a buffer layer on the substrate, wherein the buffer layer includes In;

a ternary layer on the buffer layer, wherein the ternary layer includes Ga, In, and N; and

a quaternary layer on the ternary layer, wherein the quaternary layer includes Ga, Al, In, and N.

30. (New) The device of claim 29, wherein the buffer layer includes Al and N.